

MG8N6ES1

Three-Phase Bridge IGBT Power Module

Toshiba

Circuits Per Package=1

V(BR)CES (V)=1.0k

V(BR)GES (V)=20

I(C) Abs. (A) Collector Current=8.0

Absolute Max. Power Diss. (W)=80

I(CES) Min. (A)=1.0m

@V(CES) (V) (Test Condition)=1.0k

I(GES) Max. (A)=500n

@V(GES) (V) (Test Condition)=20

V(CE)sat Max. (V)=5.0

@I(C) (A) (Test Condition)=8.0

@V(GE) (Test Condition)=15

t(r) Max. (s) Rise time=.8u

t(f) Max. (s) Fall time.=1.4u

C(iee) (Max) (F)=800p

Package=MODULE-var